

THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-IR6R-S7W”

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 870 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=20mA		1.35		V
Reverse Voltage (Vr) IR=10uA	5			V
Radiated Power ¹⁾ (Po) IF=20mA	4.5			mW
Peak Wavelength (λp) IF=20mA		870		nm
Spectral Radiation Bandwidth (Δλ) IF=20mA		45		nm
Rise Time (Tr) IFp=500mA Tw=125ns,Duty=25%		15	35	ns
Fall Time (Tf) IFp=500mA Tw=125ns,Duty=25%		20	35	ns
PeakForward Voltage (Vfm) IFp=400mA Tw=100us,Duty=10%		2.3		V

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

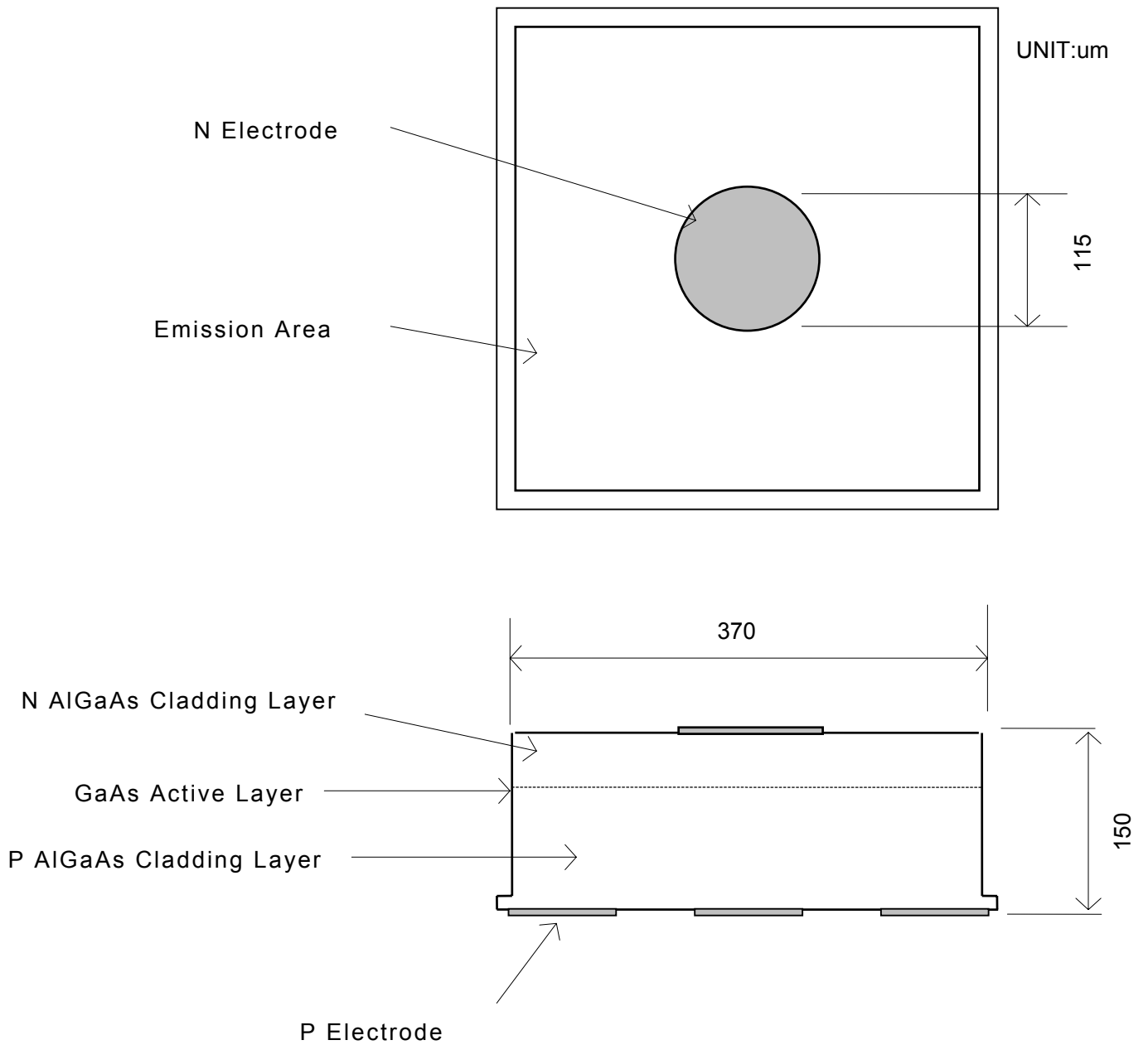
Continuous Maximum Forward Current	: 100 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1)Material : AlGaAs
- 2)Structure : Double Hetero Structure
- 3)Junction Size : 0.370mm × 0.370mm
- 4)Thickness : 0.150mm
- 5)Bond Pad Size : 0.115mm diameter
- 6)Anode Metallization : Gold Alloy
- 7)Cathode Metallization: Gold Alloy

Physical Dimensions

Model YL-IR6R-S7W



Remark: This specification is for reference purpose only, and subject to change without prior notice. Approved specification shall be obtained for the regular purchase.